

Fairchild Power Switch(SPS)

- Wide operating frequency range up to 150Khz
- Internal Burst mode Controller for Stand-by mode
- Pulse by pulse over current limiting
- Over current protection(Latch mode)
- Over voltage protection (Auto restart mode)
- Over load protection(Auto restart mode)
- Internal thermal shutdown function(Latch mode)
- Under voltage lockout
- Internal high voltage sense FET
- Eternal sync terminal/Soft start

The Fairchild Power Switch(PS) product family is specially designed for an off line SMPS with minimal external components. The Fairchild Power Switch(PS) consist of high voltage power SenseFET and current mode PWM IC. Included PWM controller features integrated fixed oscillator, under voltage lock out, optimized gate turn on/turn off driver, thermal shut down protection, over voltage protection, and temperature compensated precision current sources for loop compensation and fault protection circuitry. compared to discrete MOSFET and controller or RCC switching converter solution, a PS can reduce total component count, design size, and weight and at the same time increase efficiency, productivity, and system reliability. It has a basic platform well suited for cost effective monitor power supply.



The schematic diagram illustrates the control circuit for a power MOSFET driver. The circuit is powered by V_{cc} and V_{ref} . Key components and their functions include:

- Vref Source:** Provides a reference voltage V_{ref} for the burst mode controller and the UVLO Reset.
- Burst Mode Controller:** Consists of two comparators. The first comparator compares V_{fb} with $V_{th}=1V$. The second comparator compares V_{cc} with $V_{th}=11V/12V$. The output of the first comparator is connected to the V_{ref} input of the second comparator.
- PWM Generator:** A pulse-width modulator that takes the output of the burst mode controller and the V_{ref} input to generate a PWM signal.
- UVLO Reset:** A reset circuit that takes the output of the burst mode controller and the V_{ref} input to reset the PWM generator.
- Power-on Reset:** A reset circuit that takes the output of the burst mode controller and the V_{ref} input to reset the PWM generator.
- MOSFET Driver:** A push-pull stage consisting of two MOSFETs. The V_{ref} input is connected to the gate of the driver MOSFET. The driver MOSFET is connected to the load through R_{senese} . The MOSFET has a threshold voltage $V_{th}=1V$ and a delay I_{delay} .
- Logic and Timing:** The circuit includes several logic gates (AND, OR, NOT) and flip-flops (S-R, D) to manage the timing and control signals. A delay of $130nsec$ is specified for the filter.

Absolute Maximum Ratings

(Ta=25°C, unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-source(GND) voltage ⁽¹⁾	V _{DSS}	650	V
Drain-Gate Voltage (R _{GS} =1MΩ)	V _{DGR}	650	V
Gate-source (GND) Voltage	V _{GS}	±30	V
Drain current pulsed ⁽²⁾	I _{DM}	32.4	ADC
Single pulsed avalanche energy ⁽³⁾	E _{AS}	515	mJ
Single Pulsed Avalanche current ⁽⁴⁾	I _{AS}	25	A
Continuous drain current (T _C = 25°C)	I _D	8.1	ADC
Continuous drain current (T _C =100°C)	I _D	5.1	ADC
Supply voltage	V _{CC}	35	V
Input Voltage Range	V _{FB}	−0.3 to V _{CC}	V
	V _{S_S}	−0.3 to 10	V
Total Power Dissipation	P _D (Watt H/S)	155	W
	Derating	1.243	W/°C
Operating junction temperature	T _j	+160	°C
Operating Ambient Temperature	T _A	−25 to +85	°C
Storage Temperature range	T _{STG}	−55 to +150	°C

Notes:

1. T_j=25°C to 150°C
2. Repetitive rating: Pulse width limited by maximum junction temperature
3. L=14.5mH, starting T_j=25°C
4. L=13uH, starting T_j=25°C

Electrical Characteristics (SFET part)

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	650	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =650V, V _{GS} =0V	-	-	200	μA
		V _{DS} =520V V _{GS} =0V, T _C =125°C	-	-	300	μA
Static drain-source on resistance ^(note)	R _{DS(ON)}	V _{GS} =10V, I _D =1.8A	-	1.0	1.2	Ω
Forward transconductance ^(note)	g _{fs}	V _{DS} =50V, I _D =1.8A	-	-	-	S
Input capacitance	C _{iss}	V _{GS} =0V, V _{DS} =25V, f = 1MHz	-	1300	-	pF
Output capacitance	C _{oss}		-	135	-	
Reverse transfer capacitance	C _{rss}		-	25	-	
Turn on delay time	t _{d(on)}	V _{DD} =325V, I _D =6.5A (MOSFET switching time are essentially independent of operating temperature)	-	25	-	nS
Rise time	t _r		-	75	-	
Turn off delay time	t _{d(off)}		-	130	-	
Fall time	t _f		-	70	-	
Total gate charge (gate-source+gate-drain)	Q _g	V _{GS} =10V, I _D =6.5A, V _{DS} =520V (MOSFET Switching time are Essentially independent of Operating temperature)	-	45	60	nC
Gate-source charge	Q _{gs}		-	8	-	
Gate-drain (Miller) charge	Q _{gd}		-	21	-	

Note:

Pulse test : Pulse width ≤ 300μS, duty 2%

$$S = \frac{1}{R}$$

Electrical Characteristics

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
UVLO SECTION						
Start threshold voltage	VSTART	VFB=GND	14	15	16	V
Stop threshold voltage	VSTOP	VFB=GND	8	9	10	V
SENSEFET SECTION						
Drain to PKG Breakdown voltage	BVpkg	60HZ AC, Ta=25°C	3500	-	-	V
Drain to Source Breakdown voltage	BVdss	Vdrain = 650V, Ta=25°C	650	-	-	V
Drain to Source Leakage current	Idss	Vdrain = 650V, Ta=25°C	-	-	300	uA
OSCILLATOR SECTION						
Initial Frequency	FOSC	-	22	25	28	kHz
Voltage Stability	FSTABLE	12V ≤ Vcc ≤ 23V	0	1	3	%
Temperature Stability (note4)	ΔFOSC	-25°C ≤ Ta ≤ 85°C	0	±5	±10	%
Maximum duty cycle	DMAX	-	92	95	98	%
Minimum Duty Cycle	DMIN	-	-	-	0	%
FEEDBACK SECTION						
Feedback source current	IFB	VFB=GND	0.7	0.9	1.1	mA
Shutdown Feedback voltage	VSD	Vfb ≥ 6.9V	6.9	7.5	8.1	V
Shutdown delay current	Idelay	VFB=5V	1.6	2.0	2.4	μA
PROTECTION SECTION						
Over Voltage Protection	VOVP	Vsync ≥ 11V	27	30	33	V
Over Current Latch Voltage (Note2)	VOCL	-	0.9	1.0	1.1	V
Thermal Shutdown Temp.(Note4)	TSD	-	140	160	-	°C

Electrical Characteristics (Continued)

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Sync & SOFTSTART SECTION						
Softstart Vortage	VSS	Vfb=2	4.7	5.0	5.3	V
Softstart Current	ISS	Vss=V	0.8	1.0	1.2	mA
Sync High Threshold Voltage	VSYNCH	Vcc=16V,Vfb=5V	-	7.2	-	V
Sync Low Threshold Voltage	VSYNCL	Vcc=16V,Vfb=5V	-	5.8	-	V
BURST MODE SECTION						
Burst mode Low Threshold Voltage	VBURL	Vfb=0V	10.4	11.0	11.6	V
Burst mode High Threshold Voltage	VBURH	Vfb=0V	11.4	12.0	12.6	V
Burst mode Enable Feedback Voltage(Note4)	VBEN	Vcc=10.5V	0.7	1.0	1.3	V
Burst mode Peak Current Limit(Note3)	IBU_PK	Vcc=10.5V	0.6	0.85	1.1	V
Burst mode Frequency	FBUR	Vcc=10.5V, Vfb=0V	40	50	60	KHz
CURRENT LIMIT(SELF-PROTECTION)SECTION						
Peak Current Limit(Note3)	I _{OVER}	-	5.28	6.0	6.72	A
TOTAL DEVICE SECTION						
Start Up current	I _{START}	Vfb=GND, VCC=14V	-	0.1	0.17	mA
Operating supply current (Note1)	I _{OP}	Vfb=GND, VCC=16V	-	10	15	mA
	I _{OP(MIN)}	Vfb=GND, VCC=10V				
	I _{OP(MAX)}	Vfb=GND, VCC=28V				

Note:

- (1) These parameters is the current flowing in the Control IC.
- (2) These parameters, although guaranteed, are tested in EDS(wafer test) process.
- (3) These parameters indicate Inductor Current.
- (4) These parameters, although guranteed at the design, are not tested in massing production.

Typical Performance Characteristics

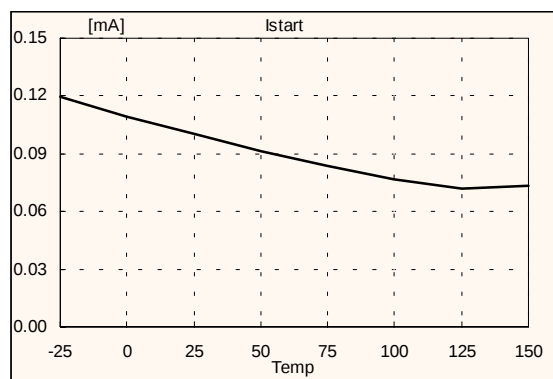


Figure 1. Start Up Current vs. Temp.

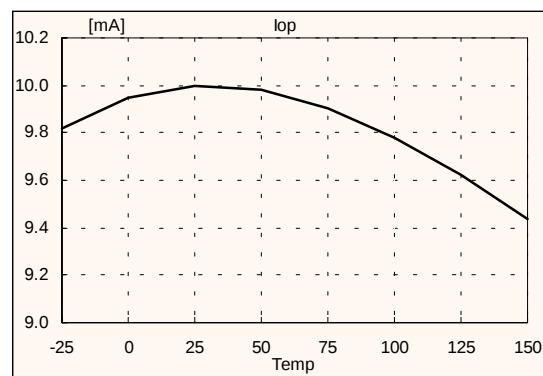


Figure 2. Operating Supply Current vs. Temp.

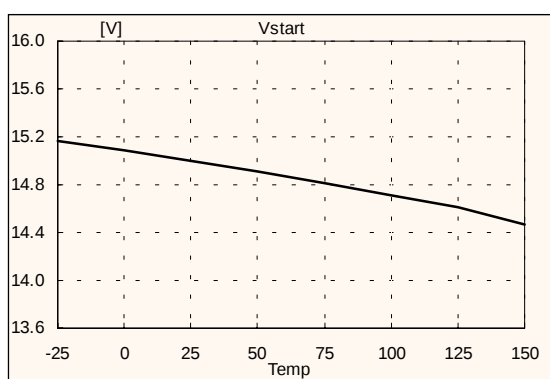


Figure 3. Start Threshold Voltage vs. Temp.

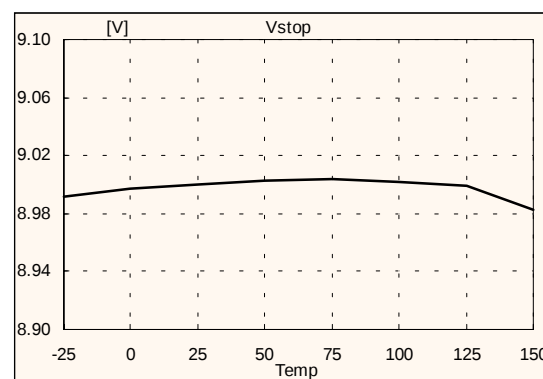


Figure 4. Stop Threshold Voltage vs. Temp.

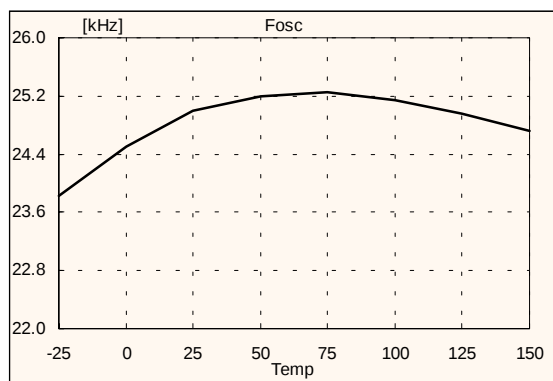


Figure 5. Initial Frequency vs. Temp.

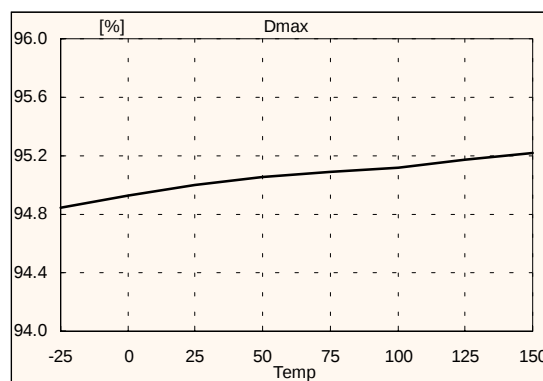


Figure 6. Maximum Duty vs. Temp.

Typical Performance Characteristics (Continued)

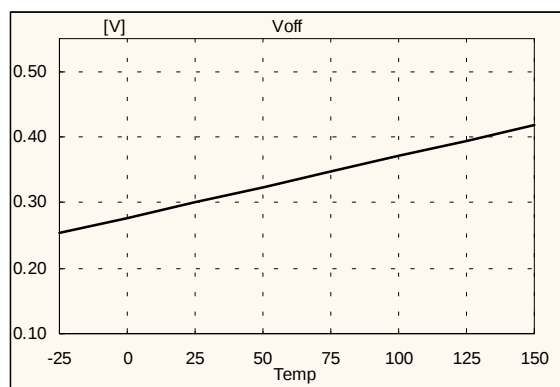


Figure 7. Feedback Offset Voltage vs. Temp.

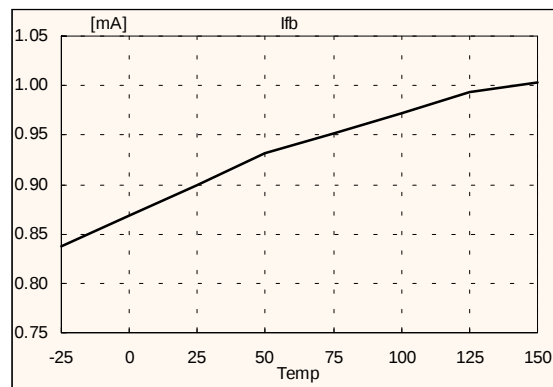


Figure 8. Feedback Source Current vs. Temp.

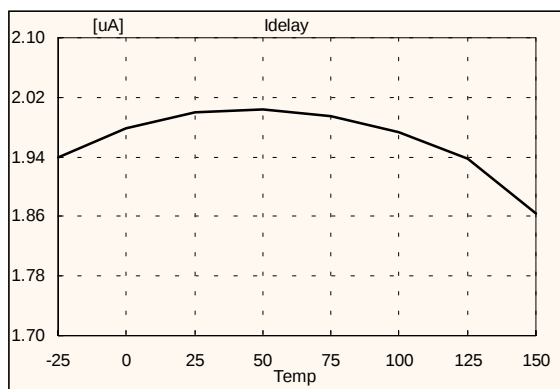


Figure 9. Shutdown Delay Current vs. Temp.

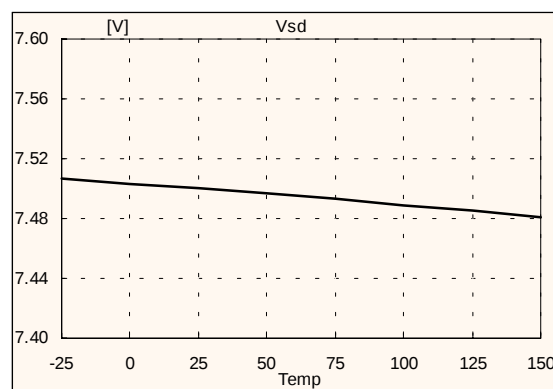


Figure 10. Shutdown Feedback Voltage vs. Temp.

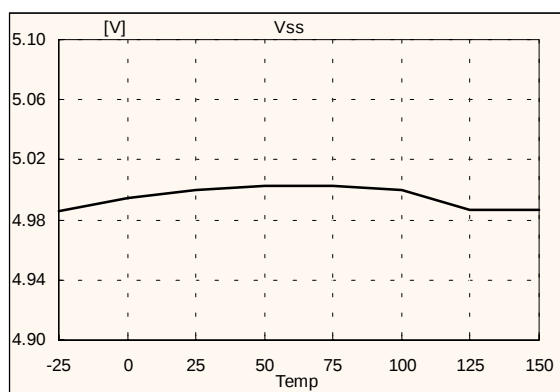


Figure 11. Softstart Voltage vs. Temp.

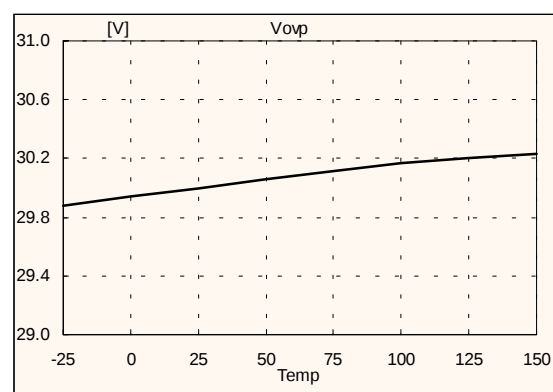


Figure 12. Over Voltage Protection vs. Temp.

Typical Performance Characteristics (Continued)

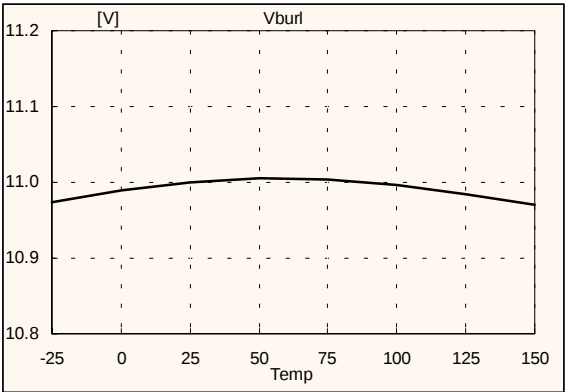


Figure 13. Burst Mode Low Voltage vs. Temp.

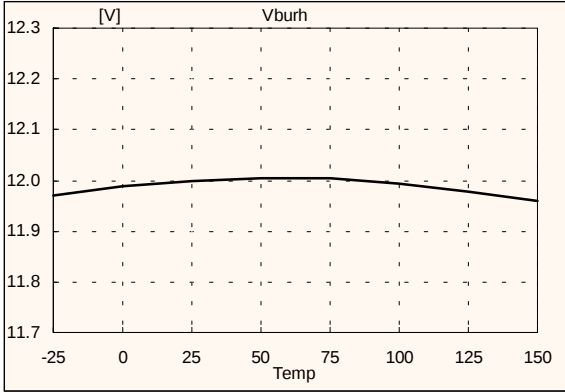


Figure 14. Burst Mode High Voltage vs. Temp.

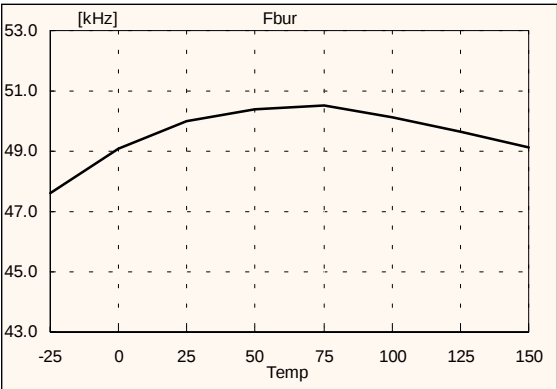


Figure 15. Burst Mode Frequency vs. Temp.

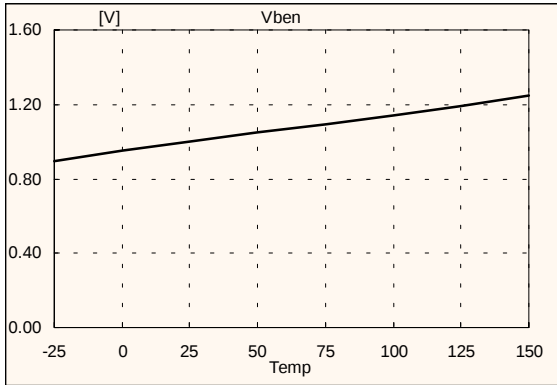


Figure 16. Burst Mode Enable Voltage vs. Temp.

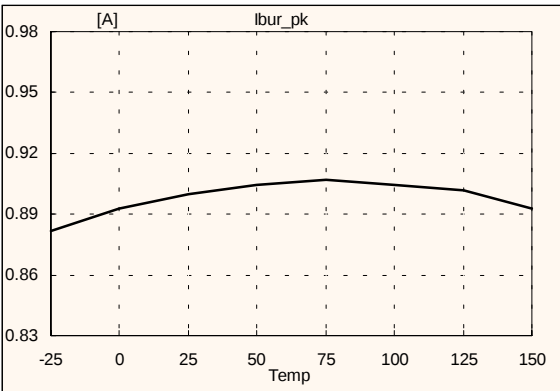


Figure 17. Burst Mode Peak Current vs. Temp.

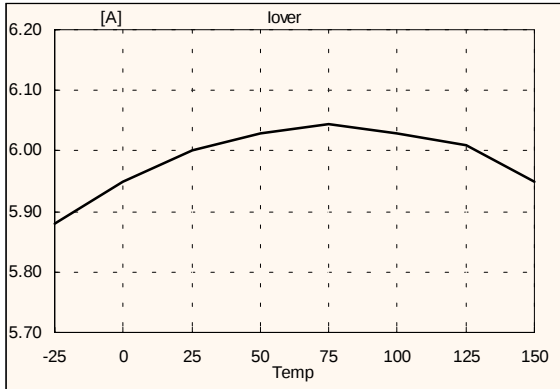
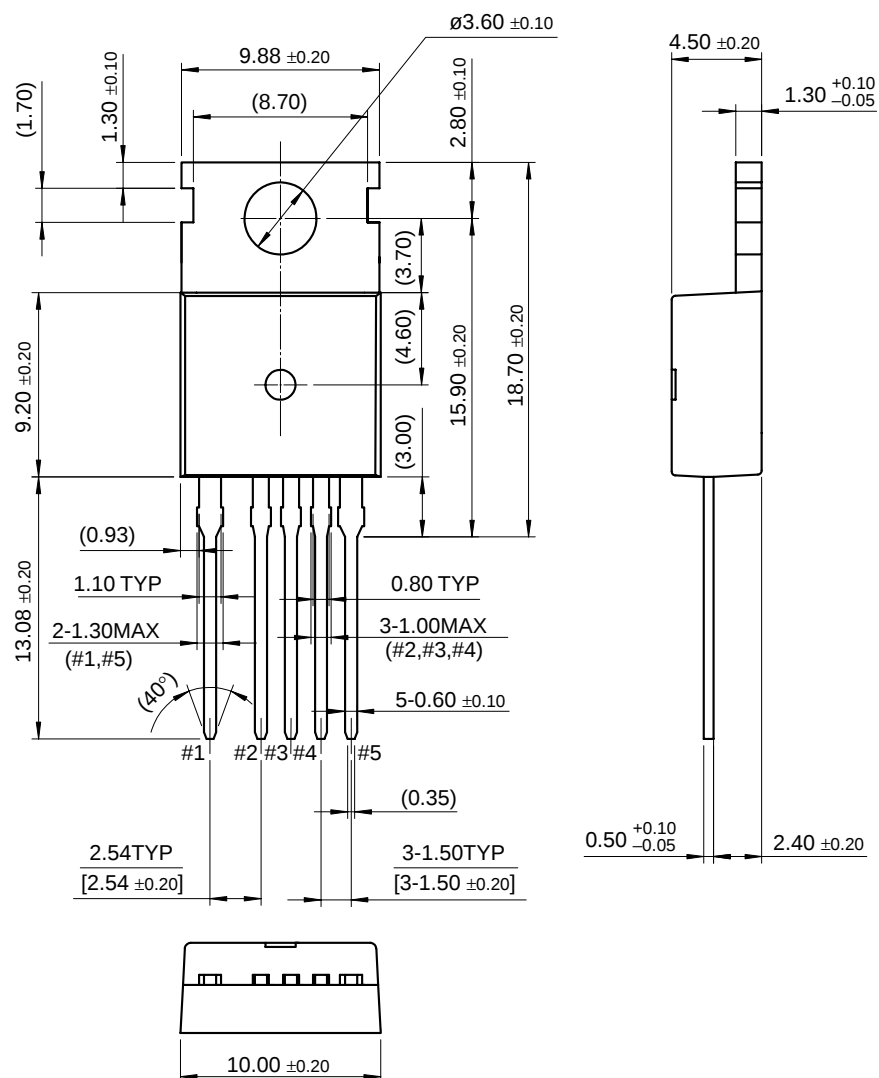


Figure 18. Peak Current Limit vs. Temp.

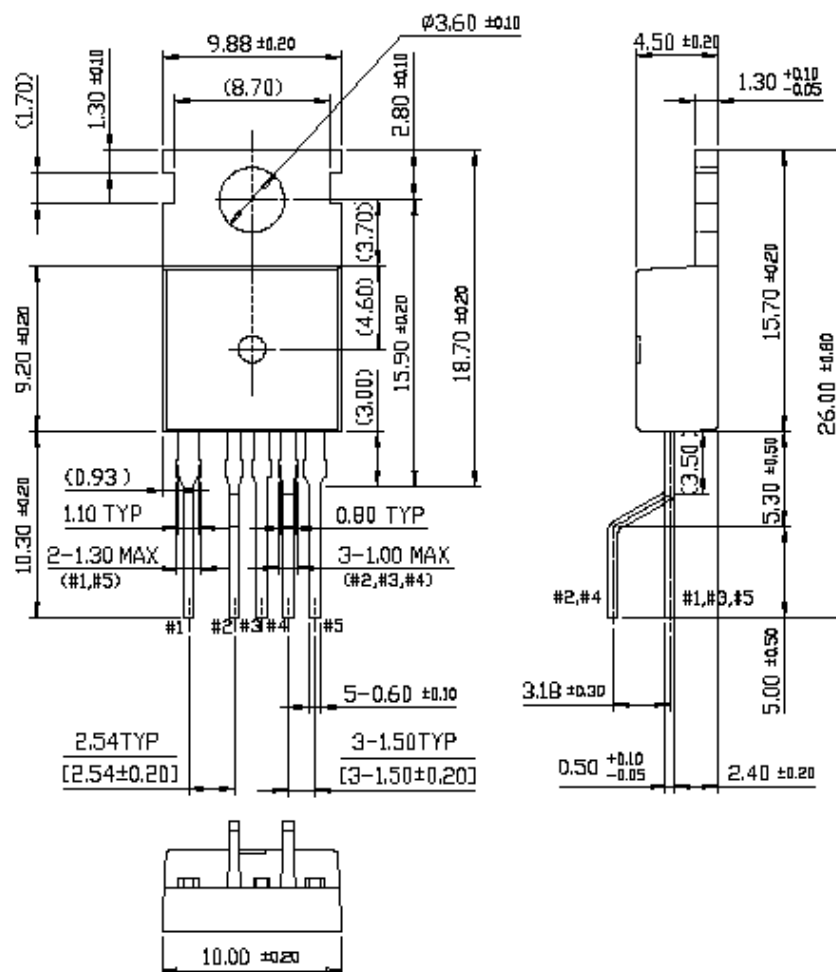
Package Dimensions

TO-220-5L



Package Dimensions (Continued)

TO-220-5L(Forming)



Ordering Information

Product Number	Package	Marking Code	BVdss	Rds(on)
FS6S0965RC-TU	TO-220-5L	6S0965RC	650V	1.0
FS6S0965RC-YDTU	TO-220-5L(Forming)			

TU : Non Forming Type

YDTU : Forming Type

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2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.